

MM54HC08/MM74HC08 Quad 2-Input AND Gate

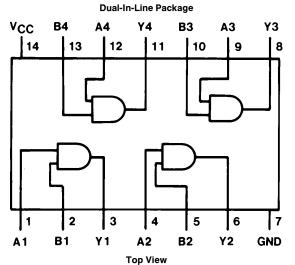
General Description

These AND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. The HC08 has buffered outputs, providing high noise immunity and the ability to drive $10\,\text{LS-TTL}$ loads. The 54HC/74HC logic family is functionally as well as pinout compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 7 ns (t_{PHL}), 12 ns (t_{PLH})
- Fanout of 10 LS-TTL loads
- \blacksquare Quiescent power consumption: 2 μ A maximum at room temperature
- Low input current: 1 μA maximum

Connection Diagram



TL/F/5297-1

Order Number MM54HC08 or MM74HC08

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5 to $+7.0$ V
DC Input Voltage (V _{IN})	-1.5 to $V_{\rm CC}$ $+$ $1.5V$
DC Output Voltage (VOUT)	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current (I _{IK} , I _{OK})	\pm 20 mA
DC Output Current, per pin (IOUT)	\pm 25 mA
DC V _{CC} or GND Current, per pin (I _{CC})	\pm 50 mA
Storage Temperature Range (T _{STG})	-65°C to $+150$ °C

Power Dissipation (P_D) (Note 3) 600 mW

 S.O. Package only
 500 mW

 Lead Temp. (T_L) (Soldering 10 seconds)
 260°C

Operating Conditions

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	Min	Max	Units
Supply Voltage (V _{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0 V _{CC}		V
Operating Temp. Range (TA)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times			
(t_r, t_f) $V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	v _{cc}	T _A = 25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units	
				Тур		Guaranteed Limits			
V_{IH}	Minimum High Level		2.0V		1.5	1.5	1.5	٧	
Input Vol	Input Voltage		4.5V 6.0V		3.15 4.2	3.15 4.2	3.15 4.2	V V	
V _{IL}	Maximum Low Level		2.0V		0.5	0.5	0.5	V	
	Input Voltage**		4.5V 6.0V		1.35 1.8	1.35 1.8	1.35 1.8	V V	
V _{OH} Minimum High Lo Output Voltage	Minimum High Level Output Voltage	V _{IN} =V _{IH} I _{OUT} ≤20 μA	2.0V	2.0	1.9	1.9	1.9	V	
		10011 = 7	4.5V 6.0V	4.5 6.0	4.4 5.9	4.4 5.9	4.4 5.9	V	
		$V_{IN} = V_{IH}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V V	
V _{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V V	
I _{IN}	Maximum Input Current	V _{IN} =V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μΑ	
Icc	Maximum Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{OUT} =0 μA	6.0V		2.0	20	40	μΑ	

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

 $\textbf{Note 3:} \ \ \text{Power Dissipation temperature derating} \\ -- \text{plastic "N" package:} \\ -- 12 \ \text{mW/°C from 65°C to 85°C; ceramic "J" package:} \\ -- 12 \ \text{mW/°C from 100°C to 125°C.} \\ -- 12 \ \text{mW/°C f$

Note 4: For a power supply of 5V \pm 10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

Note 2: Unless otherwise specified all voltages are referenced to ground.

^{**} V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $v_{CC}\!=\!5\text{V},\,T_{A}\!=\!25^{\circ}\text{C},\,C_{L}\!=\!15\,\text{pF},\,t_{r}\!=\!t_{f}\!=\!6\,\text{ns}$

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL}	Maximum Propagation Delay, Output High to Low		12	20	ns
t _{PLH}	Maximum Propagation Delay, Output Low to High		7	15	ns

AC Electrical Characteristics $V_{CC} = 2.0V$ to 6.0V, $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)

Symbol	Parameter	Conditions	V _{CC} T _A = 25°C		25°C	74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units
				Тур	Typ Guaranteed Limits			
t _{PHL}	Maximum Propagation Delay, Output High to Low		2.0V 4.5V 6.0V	77 15 13	121 24 20	151 30 25	175 35 30	ns ns ns
t _{PLH}	Maximum Propagation Delay, Output Low to High		2.0V 4.5V 6.0V	30 10 8	90 18 15	113 23 19	134 27 23	ns ns ns
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	30 8 7	75 15 13	95 19 16	110 22 19	ns ns ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		38				pF
C _{IN}	Maximum Input Capacitance			4	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$.

Physical Dimensions inches (millimeters) 0.785 (19.939) MAX [14] [13] [12] [11] [10] [9] [8] 0.025 (0.635) RAD 0.220-0.310 (5.588-7.874) 1 2 3 4 5 6 7 0.290-0.320 0.005 0.200 (D.127) MIN (5.080) MAX 0.020-0.060 (7.366-8.128) GLASS 0.060 ±0.005 (1.524 ±0.127) 0.180 (0.508 - 1.524)MA 0.008-0.012 10° MAX (0.203-D.305) 0.310-0.410 D.018 ±0.003 0.125-0.200 0.098 (7.874 - 10.41)(0.457 ±0,076) (3.175-5.080) (2.489) MAX BOTH ENDS 0.100 ±0.010 0.150 (3.81) J14A (REV G) MIN Order Number MM54HC08J or MM74HC08J NS Package J14A 14 13 12 11 10 9 0.250 ± 0.010 (6.350 ± 0.254) 1 2 3 4 5 6 7 $\frac{0.092}{(2.337)}$ DIA $\frac{0.030}{(0.762)}$ MAX 0.008 - 0.016 (0.203 - 0.406) TYP 0.125 - 0.150 (3.175 - 3.810) 0.075±0.015 (1.905±0.381) 0.014 - 0.023 (0.356 - 0.584) TYP -0.050 ± 0.010 (1.270 - 0.254) 0.325 + 0.0 Order Number MM74HC08N NS Package N14A

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